Serial No. 10/009,326
Docket No. BERGLUNDS P9918
Voluntary Amendment and Interview Summary

AMENDMENTS TO THE SPECIFICATION:

Please amend the paragraph beginning at page 2, line 27, as follows:

DESCRIPTION OF THE PREFERRED EMBODIMENTS

Sensor chip

HAYES SOLOWAY

The MOSFETs array gas sensor $\underline{10}$ realized (Fig. 1) has been designed in the aim of reducing the source and drain leakage currents and the power consumption of this type of gas sensors. Each device consists of 4 GasFETs, a temperature sensor (diode) and a heater. The actual chip size is $4.0 \times 4.0 \text{ mm}^2$.

Please amend the paragraph beginning at page 3, line 1, as follows:

Electronic components

The heater is a semiconducting resistor, which is made during the p-well implantation of the MOSFET fabrication process. The transistors (NMOS) and the diode temperature sensor are made in a single diffusion step of doping atoms from CVD oxide films. Arrays with 4 medium or small MOSFETs 12 have been designed respectively with a channel length of 13.0 and 5.0 µm. The fabrication of NMOS transistors in a p-well technology allows to drive them separately. Their source/drain leakage currents have been limited by minimizing the p-n junction surface at the source and the drain regions. Therefore, the metal/semiconductor contacts are directly taken on the source and the drain just beside the gate. GasFETs operate with their drain and gate connected together with a constant current bias between the source and the drain. In this design, the drain and gate were not connected together to allow more flexibility during the characterization of the MOSFETs electrical properties.

HAYES SOLOWAY P.C. 130 W. CUSHING STREET TUCSON, AZ 85701 TEL 520.882.7623 FAX. 520.882.7643

175 CANAL STREET
MANCHESTER, NH 03101
TEL 603.668.1400
FAX. 603.668.8567

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Please amend the paragraph beginning at page 3, line 15, as follows:

The thermal mass and therefore the power consumption of the sensor are minimized by the design. The GasFETs, the heater and the diode are located in a silicon island $\underline{18}$ isolated from the chip frame by a dielectric membrane $\underline{20}$. The membrane is made of LPCVD low-stress silicon nitride. A PECVD silicon nitride film is used as a passivation layer on the aluminum metallization $\underline{24}$. The membrane size is $1.8 \times 1.8 \text{ mm}^2$ and the silicon island area is $900 \times 900 \ \mu\text{m}^2$ and $10 \ \mu\text{m}$ thick.

Please amend the paragraph beginning at page 3, line 33, as follows:

The process starts with the implantation of boron in a 4" silicon substrate 30 (25 Ω cm, n type, 300 μ m thick double face polished) to form the MOSFETs p-well, the p side of the diode and the resistive heater. Also included in this first part is the deposition and patterning of boron and phosphorus doped CVD oxide films and the diffusion of the doping atoms to form the n+ and p+ regions of the electronic devices.

Please amend the paragraph beginning at page 5, line 22, as follows:

The design, fabrication and characterization of a low-power consumption MOSFETs array gas sensor have been presented. The sensor consists of a heating resistor, a diode temperature sensor and 4 GasFETs located in a silicon island thermally isolated from the chip frame by a dielectric membrane 14. The combination of microelectronics and MEMS (silicon bulk micro-machining) fabrication technologies was used to fabricate these devices. The array of 4 GasFETs has a low-power consumption of 80 mW at an operating temperature of 175°C. The silicon island also provides a uniform temperature all over the sensing area. The low thermal mass of the device allows the operation of the sensors in a temperature cycling mode.

HAYES SOLOWAY P.C. 130 W. CUSHING STREET TUCSON, AZ 85701 TEL 520.882.7623 FAX, \$20.882.7643

175 CANAL STREET MANCHESTER, NH 03101 TEL. 603.668.1400 FAX. 603.668.8567